



### Low Cost Low Power Instrumentation Amplifier

#### FEATURES

-Pin-to-pin compatible with industry standard AD620

#### EASY TO USE

-Gain Set with One External Resistor :

$$G = 1 + (49,4 \text{ k}\Omega / R_G) \quad (\text{Gain Range } 1 \text{ to } 1000)$$

-Wide Power Supply Range ( $\pm 2.3 \text{ V}$  to  $\pm 18 \text{ V}$ )

-Higher Performance than Three Op Amp IA Designs

-Available in 8-Lead SOIC Packaging

-Low Power

#### EXCELLENT DC PERFORMANCE ("B GRADE")

-50  $\mu\text{V}$  max, Input Offset Voltage

-0.6  $\mu\text{V}/^\circ\text{C}$  max, Input Offset Drift

-0,8 nA max, Input Bias Current

-100 dB min Common-Mode Rejection Ratio ( $G = 10$ )

#### LOW NOISE

-9 nV/Hz<sup>0,5</sup>, @ 1 kHz, Input Voltage Noise

-0.28  $\mu\text{V}$  p-p Noise (0.1 Hz to 10 Hz)

#### APPLICATIONS

-Weigh Scales

-ECG and Medical Instrumentation

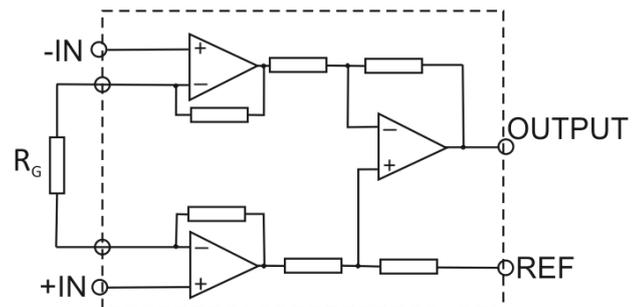
-Transducer Interface

-Data Acquisition Systems

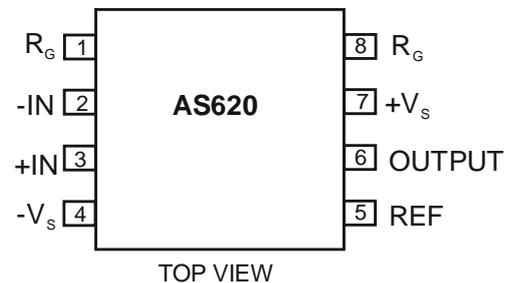
-Industrial Process Controls

-Battery Powered and Portable Equipment

Block diagram AS620



CONNECTION DIAGRAM  
DIP-8, SOIC-8 Packages



AS620AR, AS620BR: SOIC-8  
AS620AN, AS620BN: DIP-8



### SPECIFICATION

**Table 1.**  $V_s = \pm 16.5\text{ V}$ ,  $V_{REF} = 0\text{ V}$ ,  $T_A = +25^\circ\text{C}$ ,  $G = 1$ ,  $R_L = 2\text{ k}\Omega$ , unless otherwise noted.

Parameter, Unit	Symbol	Conditions	AS620A		AS620B	
			Min	Max	Min	Max
GAIN Gain Range, V/V Gain Error <sup>1)</sup> G=1 ,% Overtemperature G=10, G=100 ,% Overtemperature G=1000 ,% Overtemperature Gain Nonlinearity  G=1, G=10 G=100 G=1000	G=1 + (49,4 kΩ/R <sub>G</sub> )  GEO GE1, GE2 GE3 DL	T = +25°C V <sub>OUT</sub> = ±10 V, V <sub>s</sub> = ±15 V  T = +25°C T = -45°C to +85°C T = +25°C T = -45°C to +85°C T = +25°C T = -45°C to +85°C  V <sub>OUT</sub> = -10 V to +10 V V <sub>s</sub> = ±15 V R <sub>L</sub> = 2 kΩ R <sub>L</sub> = 2 kΩ R <sub>L</sub> = 10 kΩ				
			1	1000	1	1000
				0,1		0,02
				0,2		0,12
				0,3		0,15
				0,8		0,5
				0,7		0,5
				1,2		1,0
VOLTAGE OFFSET Input Offset, μV Overtemperature Average TC, μV/°C Output Offset, μV  Overtemperature Average TC, μV/°C Offset RTI vs. Supply, dB G=1 G=10 G=100, G=1000	Total Vos = Vos1 + Vos0/G  Vos1 Vos01 Vos02  PSR	V <sub>s</sub> = ±4,5 V to ± 16,5 V T = -45°C to +85°C  V <sub>s</sub> = ± 16,5 V V <sub>s</sub> = ±4,5 V V <sub>s</sub> = ±4,5 V to ± 16,5 V  V <sub>s</sub> = ±2,3 V to ± 18 V				
				125		50
				185		85
				1		0,6
				1000		500
				1500		750
				2000		1000
				15		7
				80		80
	95		100			
	110		120			
INPUT CURRENT Input Bias Current, nA Overtemperature Input Offset Current, nA Overtemperature	I <sub>BIAS</sub>  I <sub>OS</sub>	T = +25°C T = -45°C to +85°C T = +25°C T = -45°C to +85°C				
				1,5		0,8
				2,5		1,5
				1,0		0,5
Input Voltage Range, V <sup>2)</sup> Overtemperature  Overtemperature	IVR	V <sub>s</sub> = ±2,3 V to ± 4,5 V T = -45°C to +85°C V <sub>s</sub> = ±4,5 V to ± 16,5 V T = -45°C to +85°C	-V <sub>s</sub> + 1,9	+V <sub>s</sub> - 1,2	-V <sub>s</sub> + 1,9	+V <sub>s</sub> - 1,2
			-V <sub>s</sub> + 2,1	+V <sub>s</sub> - 1,3	-V <sub>s</sub> + 2,1	+V <sub>s</sub> - 1,3
			-V <sub>s</sub> + 1,9	+V <sub>s</sub> - 1,4	-V <sub>s</sub> + 1,9	+V <sub>s</sub> - 1,4
			-V <sub>s</sub> + 2,1	+V <sub>s</sub> - 1,4	-V <sub>s</sub> + 2,1	+V <sub>s</sub> - 1,4
REFERNCE INPUT Reference Input Current, μA Voltage Range, V Gain to Output Error, ppm	I <sub>IN</sub> VR G <sub>tO</sub>	V <sub>IN+</sub> , V <sub>REF</sub> = 0				
				60		60
			-V <sub>s</sub> + 1,6	+V <sub>s</sub> - 1,6	-V <sub>s</sub> + 1,6	+V <sub>s</sub> - 1,6
			200		100	



# AS "ALFA RPAR"

AS620

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OUTPUT Output Swing, V  Overtemperature  Overtemperature  Overtemperature	Osw1	RL=10 kΩ, Vs=±2,3 V T = -45°C to +85°C RL=10 kΩ, Vs =±4,5 V T = -45°C to +85°C RL=10 kΩ, Vs=±18 V T = -45°C to +85°C	-Vs + 1,1	+Vs - 1,2	-Vs + 1,1	+Vs - 1,2
	Osw2		-Vs + 1,4	+Vs - 1,3	-Vs + 1,4	+Vs - 1,3
	Osw3		-Vs + 1,1	+Vs - 1,2	-Vs + 1,1	+Vs - 1,2
	Osw3		-Vs + 1,4	+Vs - 1,3	-Vs + 1,4	+Vs - 1,3
Common-Mode Rejection Ratio DC to 60 Hz with 1 kΩ Source Imbalance G=1 G=10 G=100, G=1000	CMRR	V <sub>CM</sub> = 0 V to ± 10 V V <sub>CM</sub> = 0 V to ± 10 V V <sub>CM</sub> = 0 V to ± 10 V	73		80	
			93		100	
			110		120	
NOISE Voltage Noise, 1 kHz Input Voltage Noise, nV/√Hz Output Voltage Noise, nV/√Hz RTI, μV p-p G=1 G=10 G=100÷1000	Total RTI Noise = $\sqrt{(e_{ni}^2) + (e_{no}/G)^2}$					
	eni		13		13	
	eno		100		100	
		f = 0,1 Hz to 10 Hz		6,0		6,0
		f = 0,1 Hz to 10 Hz		0,8		0,8
		f = 0,1 Hz to 10 Hz		0,4		0,4
Slew Rate, V/μs	SR		0,75		0,75	
POWER SUPPLY Operating Range, V Quiescent Current, mA Overtemperature	I <sub>cc+</sub> , I <sub>cc-</sub>		± 2,3	± 18	± 2,3	± 18
				1,6		1,6
				1,9		1,9

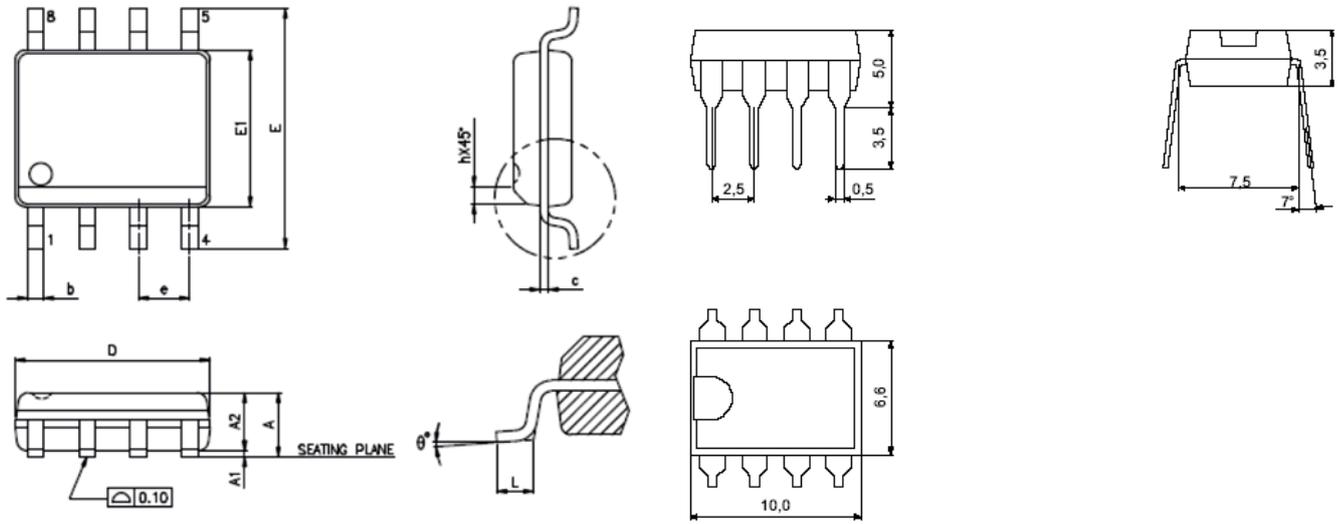
<sup>1</sup>) Does not include effects of external resistor R<sub>G</sub>.

<sup>2</sup>) One input grounded. G= 1.



### SOIC-8

### DIP-8



UNIT - mm

SYMBOLS	MIN.	MAX.
A	—	1.75
A1	0.10	0.25
A2	1.25	—
b	0.31	0.51
c	0.10	0.25
D	4.90 BSC	
E	6.00 BSC	
E1	3.90 BSC	
e	1.27 BSC	
L	0.40	1.27
h	0.25	0.50
$\theta^\circ$	0	8